

HN482764, HN482764-3, HN482764-4, HN482764G, HN482764G-3, HN482764G-4

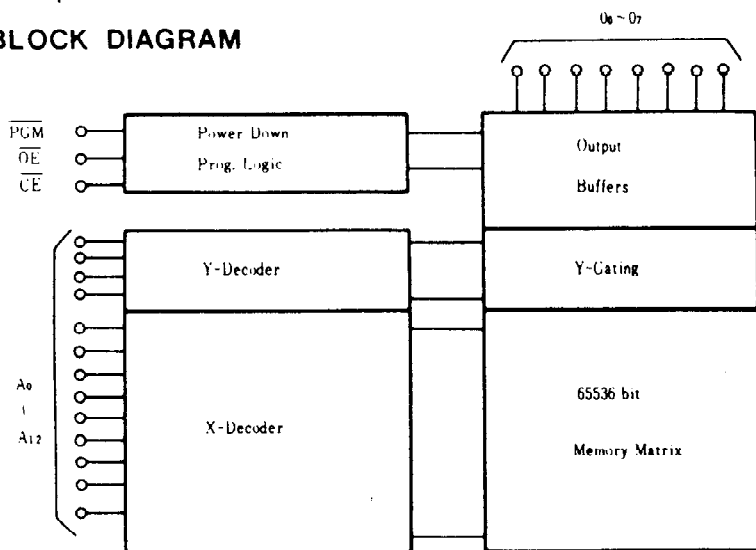
8192-word × 8-bit U. V. Erasable and Programmable Read Only Memory

The HN482764 is a 8192 word by 8 bit erasable and electrically programmable ROM. This device is packaged in a 28 pin dual-in-line package with transparent lid. The transparent lid on the package allows the memory content to be erased with ultraviolet light.

FEATURES

- Single Power Supply +5V ± 5%
- Simple Programming Program Voltage: +21V D.C.
Program with one 50ms Pulse
- Static No Clocks Required
- Inputs and Outputs TTL Compatible During Both Read and Program Mode.
- Access Time HN482764/G 250ns max
HN482764/G-3 300ns max
HN482764/G-4 450ns max
- High Performance Programming Available
- Low Standby Current 35mA max.
- Compatible with Intel 2764

BLOCK DIAGRAM



MODE SELECTION

Mode	Pins	CE (20)	OE (22)	PGM (27)	V _{PP} (1)	V _{CC} (28)	Outputs (11~13, 15~19)
Read		V _{IL}	V _{IL}	V _{IH}	V _{CC}	V _{CC}	Dout
Stand-by		V _{IH}	×	×	V _{CC}	V _{CC}	High Z
Program		V _{IL}	×	V _{IL}	V _{PP}	V _{CC}	Din
Program Verify		V _{IL}	V _{IL}	V _{IH}	V _{PP}	V _{CC}	Dout
Program Inhibit		V _{IH}	×	×	V _{PP}	V _{CC}	High Z

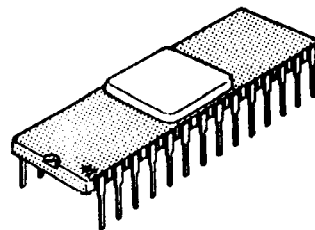
× : don't care

ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Value	Unit
Operating Temperature Range	T _{opr}	0 to +70	°C
Storage Temperature Range	T _{stg}	-65 to +125	°C
All Input and Output Voltage*	V _I	-0.3 to +7	V
V _{PP} Voltage	V _{PP}	-0.3 to +26.5	V

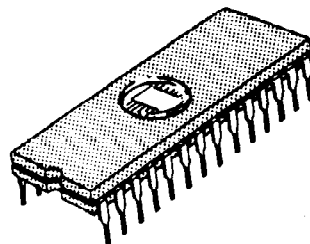
* : with respect to GND

HN482764, HN482764-3, HN482764-4



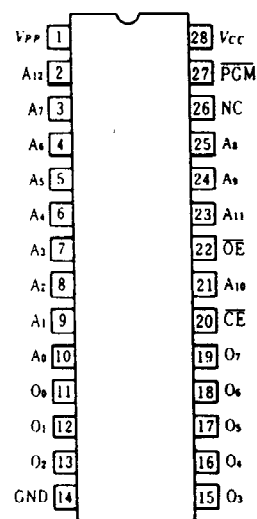
(DC-28B)

HN482764G, HN482764G-3,
HN482764G-4



(DG-28)

PIN ARRANGMENT



(Top View)

■ READ OPERATION

● DC AND OPERATING CHARACTERISTICS ($T_a=0$ to $+70^\circ\text{C}$, $V_{CC}=5\text{V}\pm 5\%$, $V_{PP}=V_{CC}\pm 0.6\text{V}$)

Parameter	Symbol	Test Condition	min	typ	max	Unit
Input Leakage Current	I_{LI}	$V_{CC}=5.25\text{V}$, $V_{iA}=5.25\text{V}$	—	—	10	μA
Output Leakage Current	I_{LO}	$V_{CC}=5.25\text{V}$, $V_{out}=5.25\text{V}/0.4\text{V}$	—	—	10	μA
V_{PP} Current	I_{PP1}	$V_{PP}=V_{CC}+0.6\text{V}$	—	—	15	mA
V_{CC} Current (Standby)	I_{CC1}	$\overline{\text{CE}}=V_{IH}$	—	—	35	mA
V_{CC} Current (Active)	I_{CC2}	$\overline{\text{CE}}=\overline{\text{OE}}=V_{IL}$	—	100	150	mA
Input Low Voltage	V_{IL}		-0.1	—	0.8	V
Input High Voltage	V_{IH}		2.0	—	$V_{CC}+1$	V
Output Low Voltage	V_{OL}	$I_{OL}=2.1\text{mA}$	—	—	0.45	V
Output High Voltage	V_{OH}	$I_{OH}=-400\mu\text{A}$	2.4	—	—	V

● AC CHARACTERISTICS ($T_a=0$ to $+70^\circ\text{C}$, $V_{CC}=5\text{V}\pm 5\%$, $V_{PP}=V_{CC}\pm 0.6\text{V}$)

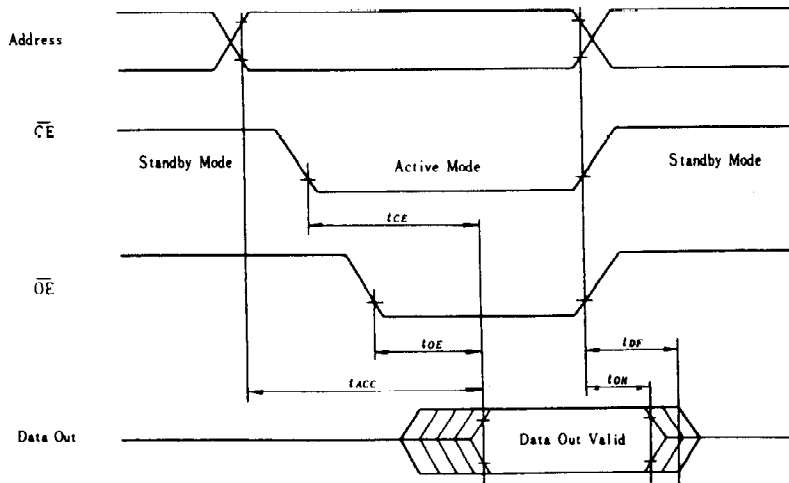
Parameter	Symbol	Test Conditions	HN482764/G		HN482764/G-3		HN482764/G-4		Unit
			min	max	min	max	min	max	
Address to Output Delay	t_{ACC}	$\overline{\text{CE}}=\overline{\text{OE}}=V_{IL}$	—	250	—	300	—	450	ns
$\overline{\text{CE}}$ to Output Delay	t_{CE}	$\overline{\text{OE}}=V_{IL}$	—	250	—	300	—	450	ns
$\overline{\text{OE}}$ to Output Delay	t_{OE}	$\overline{\text{CE}}=V_{IL}$	10	100	10	150	10	150	ns
$\overline{\text{OE}}$ High to Output Float	t_{DF}	$\overline{\text{CE}}=V_{IL}$	0	90	0	130	0	130	ns
Address to Output Hold	t_{OH}	$\overline{\text{CE}}=\overline{\text{OE}}=V_{IL}$	0	—	0	—	0	—	ns

Note: t_{OH} defines the time at which the output achieves the open circuit condition and is not referenced to output voltage levels.

● SWITCHING CHARACTERISTICS

Test Condition

- Input Pulse Levels: 0.8V to 2.2V
- Input Rise and Fall Time: $\leq 20\text{ns}$
- Output Load: 1TTL Gate + 100pF
- Reference Level for Measuring Timing: Inputs; 1V and 2V
Output; 0.8V and 2.0V



● CAPACITANCE ($T_a=25^\circ\text{C}$, $f=1\text{MHz}$)

Parameter	Symbol	Test Condition	min	typ	max	Unit
Input Capacitance	C_{iA}	$V_{iA}=0\text{V}$	—	4	6	pF
Output Capacitance	C_{out}	$V_{out}=0\text{V}$	—	8	12	pF

NOTICE

The example of an applied circuit or combination with other equipment shown herein indicates characteristics and performance of a semiconductor-applied products. The company shall assume no responsibility for any problem involving a patent caused when applying the descriptions in the example.

■ PROGRAMMING OPERATION

● DC PROGRAMMING CHARACTERISTICS ($T_a = 25^\circ\text{C} \pm 5^\circ\text{C}$, $V_{CC} = 5\text{V} \pm 5\%$, $V_{PP} = 21\text{V} \pm 0.5\text{V}$)

Parameter	Symbol	Test Condition	min	typ	max	Unit
Input Leakage Current	I_{LI}	$V_{in} = 5.25\text{V}$	—	—	10	μA
Output Low Voltage During Verify	V_{OL}	$I_{OL} = 2.1\text{mA}$	—	—	0.45	V
Output High Voltage During Verify	V_{OH}	$I_{OH} = -400\mu\text{A}$	2.4	—	—	V
V_{CC} Current (Active)	I_{CC2}		—	—	150	mA
Input Low Level	V_{IL}		-0.1	—	0.8	V
Input High Level	V_{IH}		2.0	—	$V_{CC} + 1$	V
V_{PP} Supply Current	I_{PP}	$\overline{\text{CE}} - \text{PGM} = V_{IL}$	—	—	30	mA

● AC PROGRAMMING CHARACTERISTICS ($T_a = 25^\circ\text{C} \pm 5^\circ\text{C}$, $V_{CC} = 5\text{V} \pm 5\%$, $V_{PP} = 21\text{V} \pm 0.5\text{V}$)

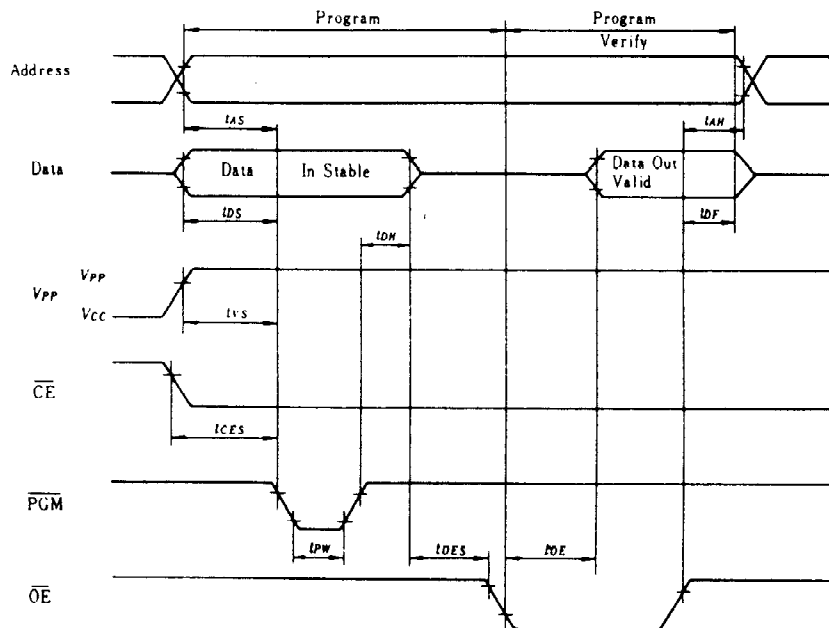
Parameter	Symbol	Test Condition	min	typ	max	Unit
Address Setup Time	t_{AS}		2	—	—	μs
$\overline{\text{OE}}$ Setup Time	t_{OES}		2	—	—	μs
Data Setup Time	t_{DS}		2	—	—	μs
Address Hold Time	t_{AH}		0	—	—	μs
Data Hold Time	t_{DH}		2	—	—	μs
$\overline{\text{OE}}$ to Output Float Delay	t_{DF}		0	—	130	ns
V_{PP} Setup Time	t_{VS}		2	—	—	μs
PGM Pulse Width During Programming	t_{PW}		45	50	55	ms
$\overline{\text{CE}}$ Setup Time	t_{CES}		2	—	—	μs
Data Valid from $\overline{\text{OE}}$	t_{OE}		—	—	150	ns

Note: t_{DF} defines the time at which the output achieves the open circuit condition and is not referenced to output voltage levels.

● SWITCHING CHARACTERISTICS

Test Condition

- Input Pulse Level: 0.8V to 2.2V
- Input Rise and Fall Time: $\leq 20\text{ ns}$
- Reference Level for Measuring Timing: Input; 1V and 2V
Output; 0.8V and 2V

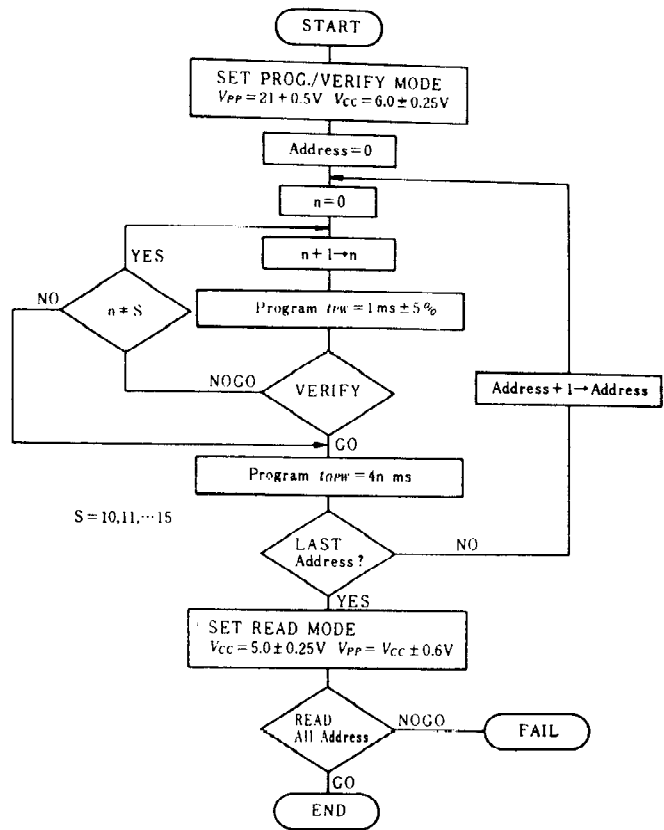


■ ERASE

Erasure of HN482764 is performed by exposure to Ultra-violet light of 2537Å, and all the output data are changed to "1" after this erasure procedure. The minimum integrated dose (i.e. UV intensity x exposure time) for erasure is $15\text{W} \cdot \text{sec}/\text{cm}^2$

■ HIGH PERFORMANCE PROGRAMMING

This device can be applied the High Performance Programming algorithm shown in following flowchart. This algorithm allows to obtain faster programming time without any voltage stress to the device nor deterioration in reliability of programmed data.



High Performance Programming Flowchart

● AC PROGRAMMING CHARACTERISTICS (T_a = 25 °C ± 5 °C, V_{CC} = 6V ± 0.25V, V_{PP} = 21V ± 0.5V)

Parameter	Symbol	Test Condition	min	typ	max	Unit
Address Setup Time	t _{AS}		2	—	—	μs
OE Setup Time	t _{OES}		2	—	—	μs
Data Setup Time	t _{DS}		2	—	—	μs
Address Hold Time	t _{AH}		0	—	—	μs
Data Hold Time	t _{DH}		2	—	—	μs
OE to Output Float Delay*	t _{OF}		0	—	130	ns
V _{PP} Setup Time	t _{VPS}		2	—	—	μs
V _{CC} Setup Time	t _{VCS}		2	—	—	μs
PGM Pulse Width during Initial Program	t _{IPW}		0.95	1.0	1.05	ms
PGM Pulse Width during Over Program**	t _{OPW}		3.8	—	63	ms
CE Setup Time	t _{CES}		2	—	—	μs
Data Valid from OE	t _{OE}		—	—	150	ns

Notes) * t_{OF} defines the time at which the output achieves the open circuit condition and is not referenced to output voltage levels.
** t_{OPW} is defined as mentioned in flow chart.

● SWITCHING CHARACTERISTICS

Test Condition

Input Pulse Level: 0.8V to 2.2V
 Input Rise and Fall Time: ≤ 20 ns
 Reference Level for Measuring Timing: Input; 1V and 2V
 Output; 0.8V and 2V

